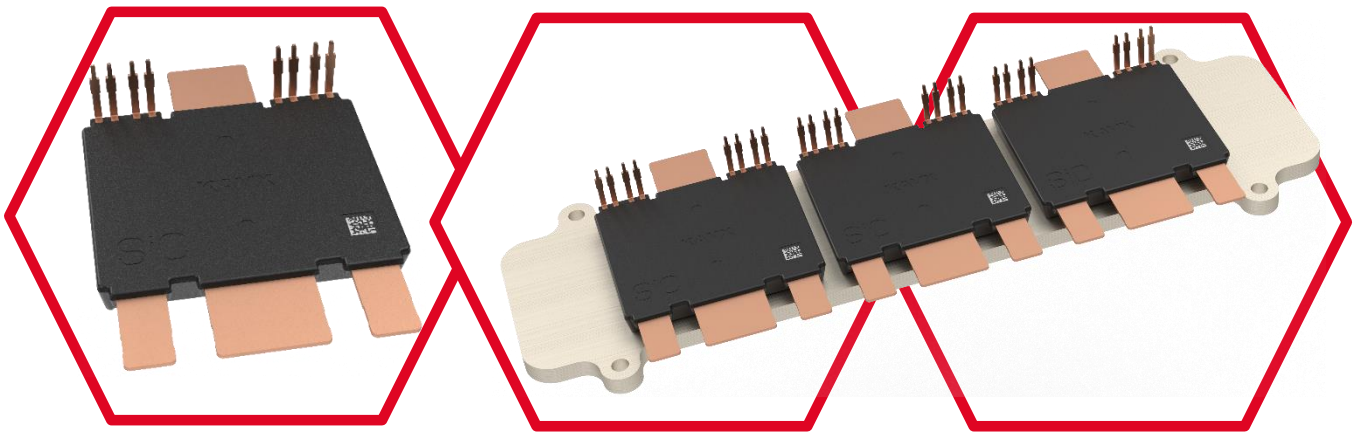
Fast Facts

Power Module for Inverters
Half bridge or B6 bridge configuration
SiC Power Module - Silicon carbide semiconductor half-bridge module: 750 V / 1200 V – up to 500 A

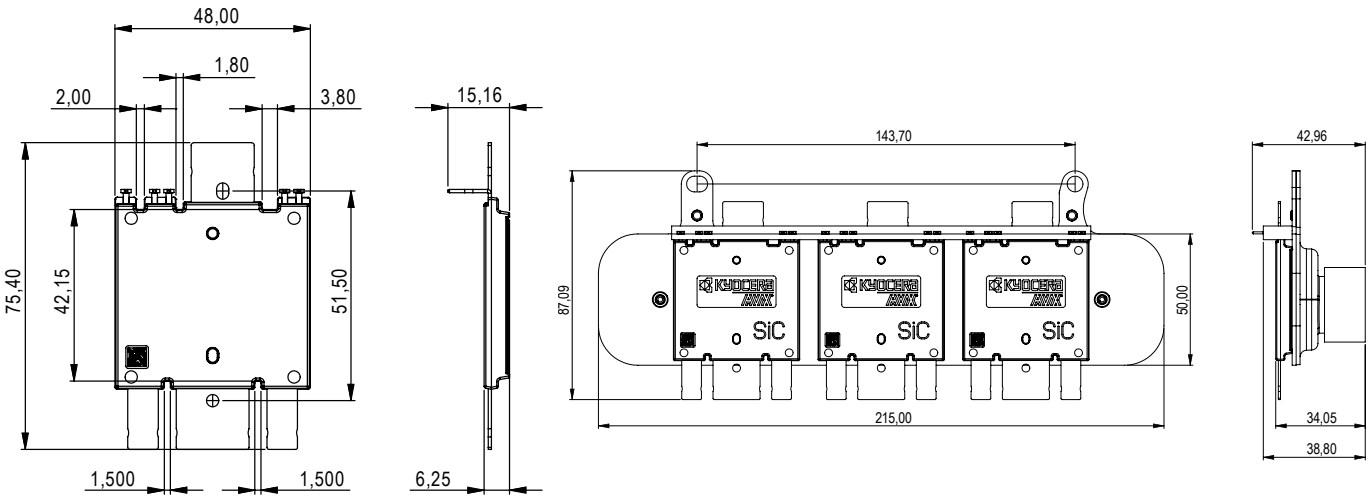


Technology

- 175 °C operating temperature
- Ultra small footprint
- Scalable circuit design
- Ultra low loss
- Silicon nitride ceramic substrate
- ECPE AQG 324 qualified

Key Technologies

- TLPS and lead frame attachment
- Low inductive lead frame and package design
- Transfer molding



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